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FAIRCHILD

SEMICONDUCTOR®

November 2013

FQPF3N25

N-Channel QFET[®] MOSFET

250 V, 2.3 A, 2.2 Ω

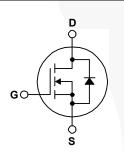
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply.

Features

- 2.3 A, 250 V, $R_{DS(on)}$ = 2.2 Ω (Max.) @ V_{GS} = 10 V, I_D = 1.15 A
- Low Gate Charge (Typ. 4.0 nC)
- Low Crss (Typ. 4.7 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

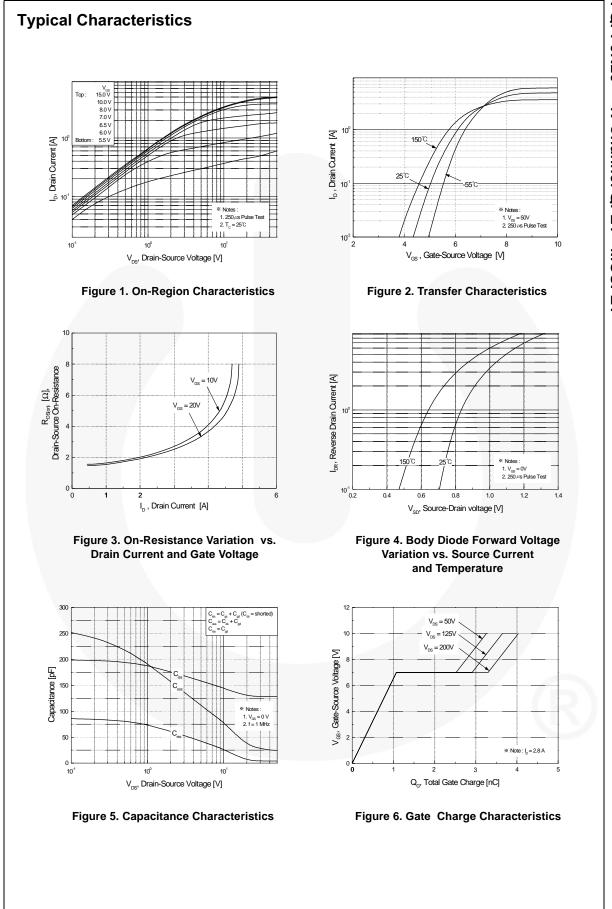
Symbol	Parameter		FQPF3N25	Unit
V _{DSS}	Drain-Source Voltage		250	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}$	°C)	2.3	A
	- Continuous (T _C = 100)°C)	1.45	A
DM	Drain Current - Pulsed	(Note 1)	9.2	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	40	mJ
AR	Avalanche Current	(Note 1)	2.3	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	2.7	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		27	W
	- Derate above 25°C		0.22	W/°C
T _J , T _{STG}	Operating and Storage Temperature Ran	nge	-55 to +150	°C
TL	Maximum lead temperature for soldering 1/8" from case for 5 seconds	j purposes,	300	°C

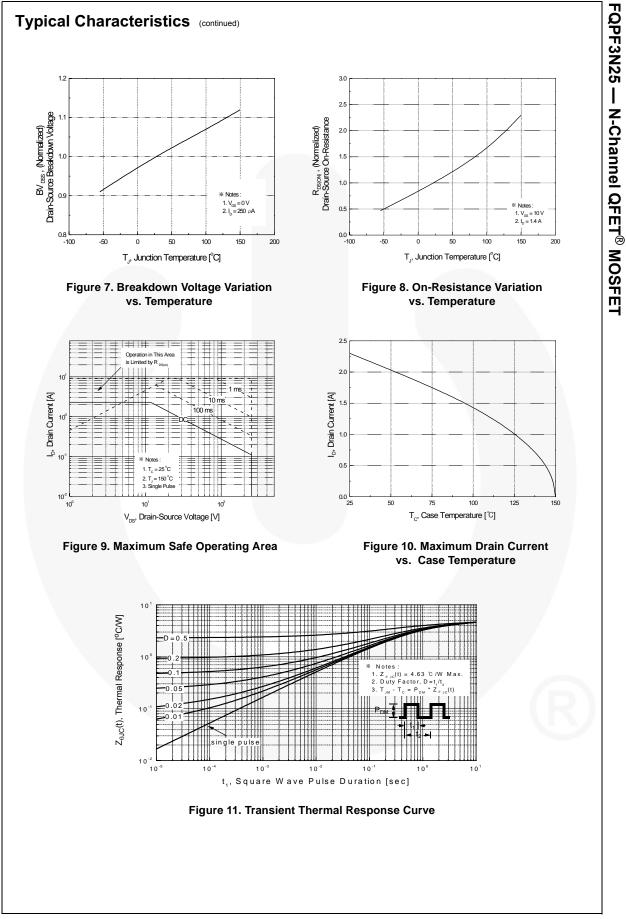
Thermal Characteristics

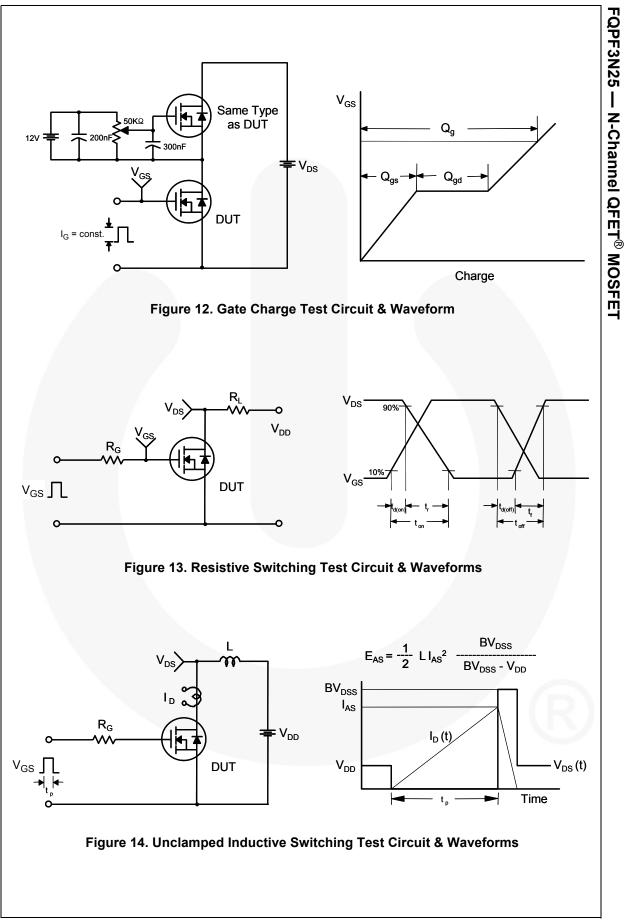
Symbol	Parameter	FQPF3N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.63	°C/W
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

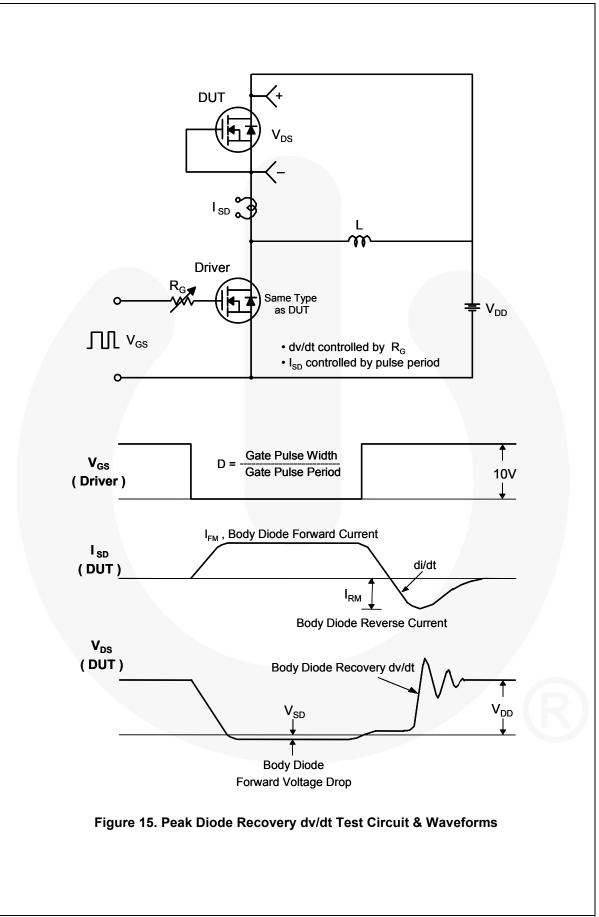
Electric Symbol Off Cha BV _{DSS} ΔBV _{DSS} ΔT _J	cal Ch	FQPF3N25		kage Packing Method	Facking Method	Reel S	JIZE	Tape W	iaui	Quantity	
Symbol Off Cha ^{BV} _{DSS} ΔBV _{DSS} / ΔΤ _J			FQPF3N25 FQPF3N25 TO-2		20F Tube N/		4	N/A		50 units	
Symbol Off Cha ^{BV} _{DSS} ΔBV _{DSS} / ΔΤ _J											
BV _{DSS} ΔBV _{DSS} / ΔT _J	rootori	aracteristics	T _c = 25°C un	less otherv	vise noted.						
ΔBV_{DSS}	rootori	Parameter			Test Conditions		Min	Тур	Max	Unit	
BV _{DSS} ΔBV _{DSS} / ΔT _J		etice									
ΔBV _{DSS} / ΔT _J				$V_{GS} =$	0 V, I _D = 250 μA		250			V	
/ ΔT _J	Breakdo	own Voltage Temperat	ure	1 0		2500		0.04		V/°C	
Ince	T _J Coefficient			$I_D = 250 \ \mu\text{A}, \text{ Referenced to } 25^{\circ}\text{C}$			0.24		V/°C		
.035	Zero Gate Voltage Drain Current			250 V, V _{GS} = 0 V				1	μA		
			$V_{DS} = 200 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$					10	μΑ		
I _{GSSF}		Gate-Body Leakage Current, Forward		$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$					100	nA	
I _{GSSR}	Gate-Bo	Gate-Body Leakage Current, Reverse		V_{GS} = -30 V, V_{DS} = 0 V					-100	nA	
On Cha	racteri	stics									
V _{GS(th)}		reshold Voltage	-	V _{DS} =	V _{GS} , I _D = 250 μA	-	3.0		5.0	V	
R _{DS(on)}		rain-Source	_		10 V, I _D = 1.15 A						
(,	On-Resistance Forward Transconductance				2			1.75	2.2	Ω	
9 _{FS}			V _{DS} =	50 V, I _D = 1.15 A			1.4		S		
Dynami	ic Char	acteristics									
C _{iss}	1		_		05.1(.)(_	130	170	pF	
C _{oss}		Input Capacitance Output Capacitance Reverse Transfer Capacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			30	40	pF		
C _{rss}	-			1 = 1.0				4.7	6.1	pF	
-155	11010100		•						0.1	p.	
Switchi	ing Cha	racteristics									
t _{d(on)}	Turn-Or	n Delay Time		Vpp =	125 V, I _D = 2.8 A,			6.6	23	ns	
t _r	Turn-Or	n Rise Time		$R_{G} = 2$	_			25	60	ns	
				0							
	Turn-Of	f Delay Time						5.5	21	ns	
t _{d(off)} t _f		f Delay Time f Fall Time				(Note 4)		5.5 20	21 50	ns ns	
t _{d(off)} t _f Q _g	Turn-Of Total Ga	f Fall Time ate Charge			200 V, I _D = 2.8 A,	(Note 4)		20 4.0			
t _{d(off)} t _f Q _g Q _{gs}	Turn-Of Total Ga Gate-Sc	f Fall Time ate Charge burce Charge		V _{DS} = V _{GS} =	200 V, I _D = 2.8 A, 10 V			20 4.0 1.1	50	ns nC nC	
t _{d(off)} t _f Q _g	Turn-Of Total Ga Gate-Sc	f Fall Time ate Charge			200 V, I _D = 2.8 A, 10 V	(Note 4) (Note 4)		20 4.0	50 5.2	ns nC	
t _{d(off)} t _f Q _g Q _{gs} Q _{gd}	Turn-Of Total Ga Gate-So Gate-Dr	f Fall Time ate Charge ource Charge rain Charge	iotico o	V _{GS} =	200 V, I _D = 2.8 A, 10 V			20 4.0 1.1	50 5.2 	ns nC nC	
t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S	Turn-Of Total Ga Gate-So Gate-Dr	f Fall Time ate Charge burce Charge rain Charge Diode Character		V _{GS} =	200 V, I _D = 2.8 A, 10 V kimum Ratings			20 4.0 1.1 2.2	50 5.2 	ns nC nC nC	
$t_{d(off)}$ t_{f} Q_{g} Q_{gs} Q_{gd} Drain-S I_{S}	Turn-Of Total Ga Gate-Sc Gate-Dr Source I Maximu	f Fall Time ate Charge burce Charge rain Charge Diode Character m Continuous Drain-S	Source Dic	V _{GS} =	200 V, I _D = 2.8 A, 10 V kimum Ratings vard Current			20 4.0 1.1 2.2	50 5.2 2.3	ns nC nC nC	
t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S I _{SM}	Turn-Of Total Ga Gate-Sc Gate-Dr Source I Maximu Maximu	f Fall Time ate Charge ource Charge rain Charge Diode Character m Continuous Drain-Source	Source Dic ce Diode F	V _{GS} =	200 V, I _D = 2.8 A, 10 V kimum Ratings vard Current Current			20 4.0 1.1 2.2	50 5.2 2.3 9.2	ns nC nC nC A A	
t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S I _S V _{SD}	Turn-Of Total Ga Gate-Sc Gate-Dr Gource I Maximu Maximu Drain-S	f Fall Time ate Charge ource Charge rain Charge Diode Character m Continuous Drain-S m Pulsed Drain-Source ource Diode Forward	Source Dic ce Diode F	V _{GS} = nd Max ode Forv Forward V _{GS} =	200 V, $I_D = 2.8 \text{ A}$, 10 V kimum Ratings vard Current Current 0 V, $I_S = 2.3 \text{ A}$			20 4.0 1.1 2.2	50 5.2 2.3 9.2 1.5	ns nC nC nC A A V	
t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S I _{SM}	Turn-Of Total Ga Gate-Sc Gate-Dr Source I Maximu Maximu Drain-Sc Reverse	f Fall Time ate Charge ource Charge rain Charge Diode Character m Continuous Drain-Source	Source Dic ce Diode F	$V_{GS} =$ nd Max pde Forw Forward $V_{GS} =$ $V_{GS} =$	200 V, I _D = 2.8 A, 10 V kimum Ratings vard Current Current		 	20 4.0 1.1 2.2	50 5.2 2.3 9.2	ns nC nC nC A A	

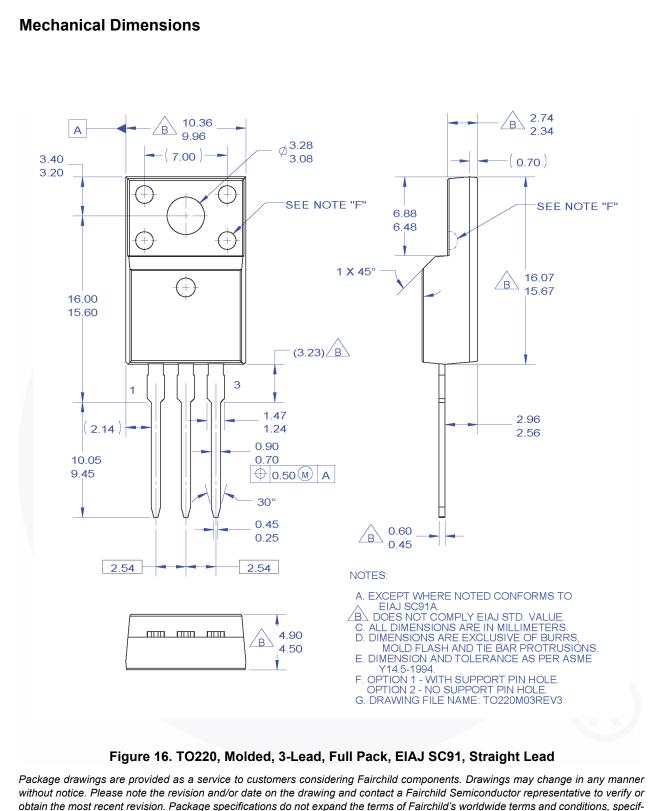
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1			Rev.

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FQPF3N25

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